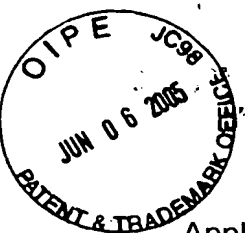


IFW



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Edward Y. CHANG et al. Confirmation No: 4041  
Appl. No. : 10/699,839  
Filed : November 4, 2003  
Title : GROWTH OF GaAs EPITAXIAL LAYERS ON Si SUBSTRATE  
BY USING A NOVEL GeSi BUFFER LAYER  
  
TC/A.U. : 2818  
Examiner : M. H. C. Tran  
  
Docket No.: : CHAN3228/REF  
Customer No: : 23364

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of May 6, 2005, in connection with the above identified application.

The Official Action is a restriction requirement in which it is urged that there are two separate and distinct inventions claimed in this application. Applicants elect the Group II invention which includes claims 1-13, without traverse. Applicants reserve the right to file a divisional application on the non-elected invention at a later time.

In view of the election of the Group II invention, without traverse, an early and favorable action on the merits is now believed to be in order and is most respectfully requested.

Respectfully submitted,  
BACON & THOMAS, PLLC

By: Richard E. Fichter  
Richard E. Fichter  
Registration No. 26,382

625 Slaters Lane, Fourth Floor  
Alexandria, Virginia 22314  
Phone: (703) 683-0500  
Facsimile: (703) 683-1080  
REF/kdd  
ResponsetoRestrictRequirement.wpd  
June 6, 2005